MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPN11003NL

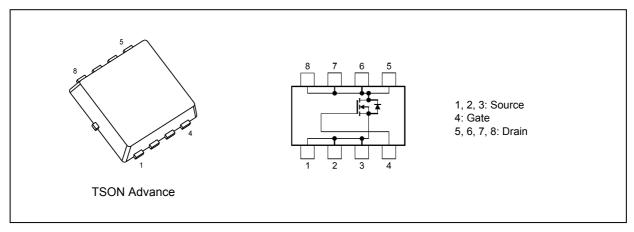
1. Applications

- Switching Voltage Regulators
- DC-DC Converters

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 2.0 \text{ nC}$ (typ.)
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 12.6 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$
- (4) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (5) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteris	tics		Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20]
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	ID	31	A
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	11	1
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	62	1
Power dissipation	(T _c = 25 °C)		PD	19	W
Power dissipation	(t = 10 s)	(Note 3)	PD	1.9	1
Power dissipation	(t = 10 s)	(Note 4)	PD	0.7	1
Single-pulse avalanche energy		(Note 5)	E _{AS}	26	mJ
Avalanche current			I _{AR}	11	A
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	6.57	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	65.7	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	178	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_DD = 24 V, T_ch = 25 °C (initial), L = 170 $\mu H, \, I_{AR}$ = 11 A

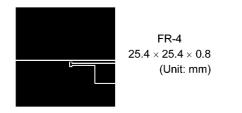


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

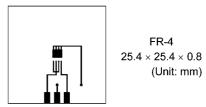


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

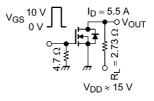
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_		±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30		_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.1 mA	1.3		2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 5 A	_	12.6	16	mΩ
		V _{GS} = 10 V, I _D = 5.5 A	_	9.4	11	

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		510	660	pF
Reverse transfer capacitance	C _{rss}]		18	50	
Output capacitance	C _{oss}]		300	_	
Gate resistance	r _g	—		1.3	2.0	Ω
Switching time (rise time)	tr	See Fig. 6.2.1		2.1	_	ns
Switching time (turn-on time)	t _{on}]		7.5	_	
Switching time (fall time)	t _f]		1.9	_	1
Switching time (turn-off time)	t _{off}]		14	_	



Duty \leq 1 %, $t_W^{}=$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

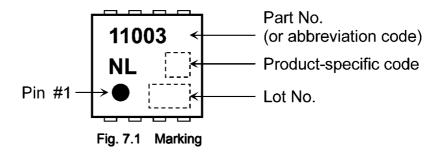
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 11 A	_	7.5	_	nC
gate-drain)		$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	—	3.3	—	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	_	2.0	_	
Gate-drain charge	Q _{gd}			1.0	_	
Gate switch charge	Q _{SW}			2.0		

6.4. Source-Drain Characteristics ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

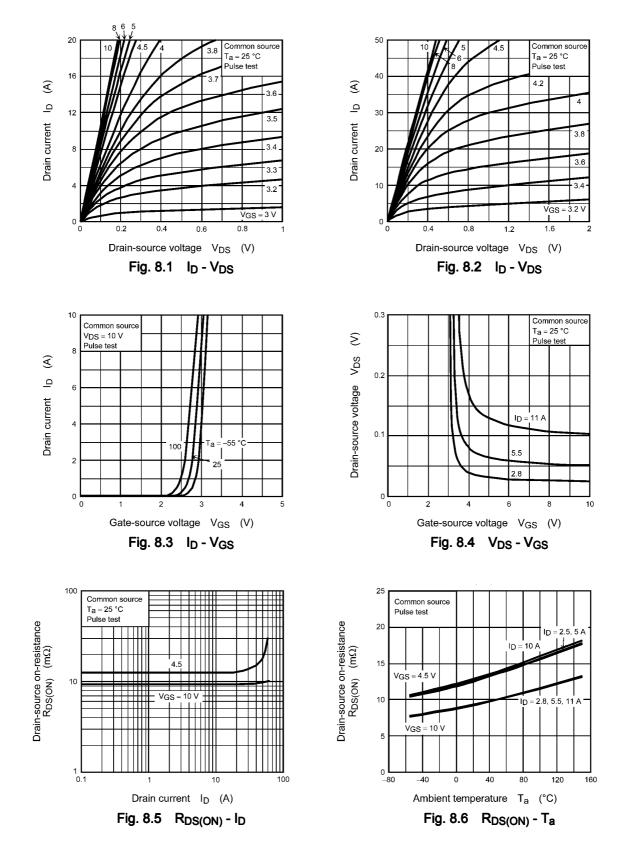
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	—	_	_	62	А
Diode forward voltage		V_{DSF}	I _{DR} = 11 A, V _{GS} = 0 V	_	_	-1.2	V

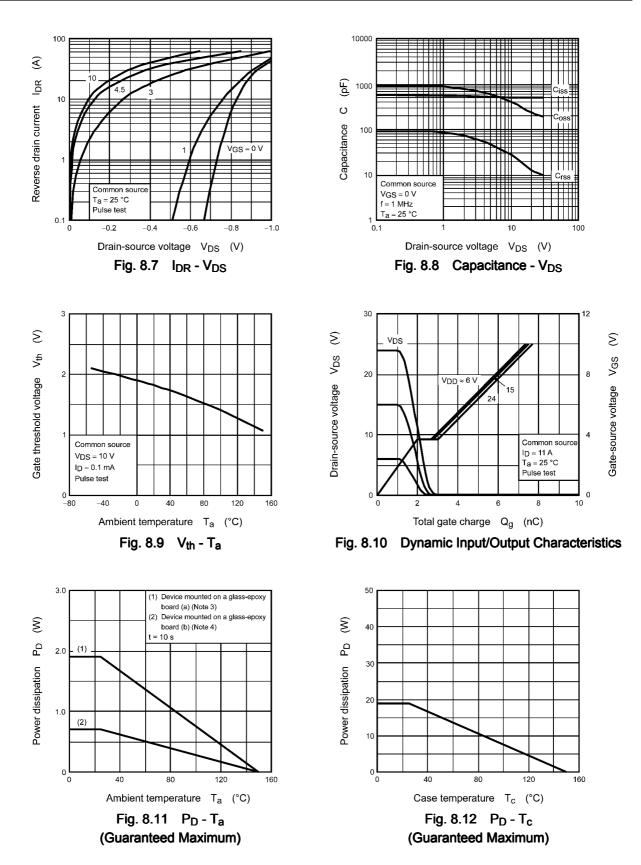
Note 6: Ensure that the channel temperature does not exceed 150 °C.

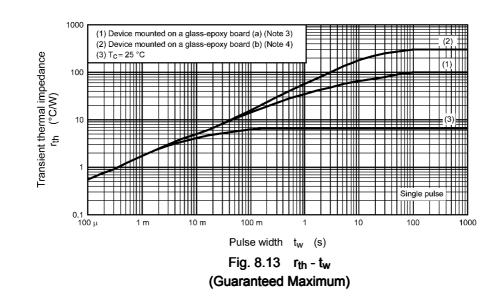
7. Marking

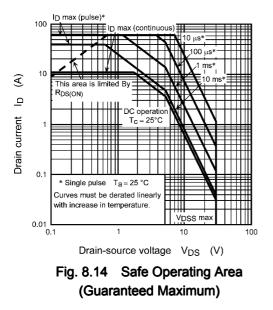


8. Characteristics Curves (Note)









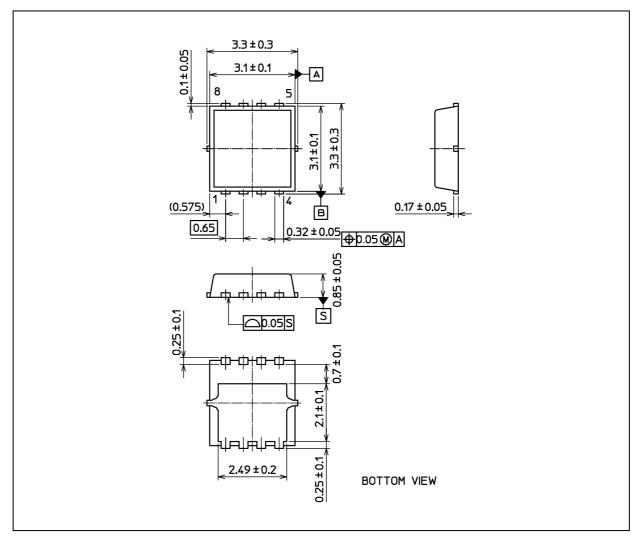
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPN11003NL

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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